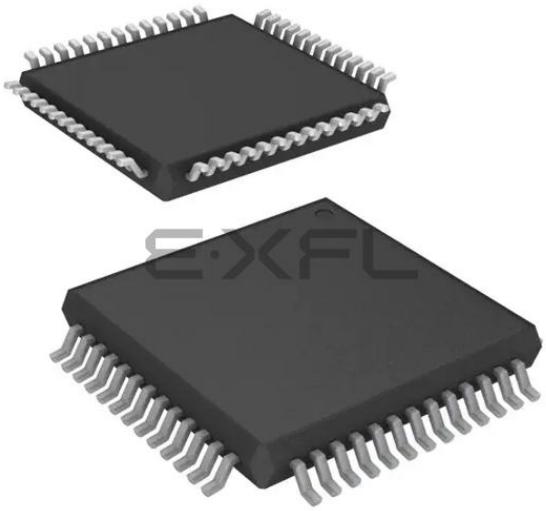
Renesas Electronics America Inc - R5F10RJCAFA#50 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rjcafa-50

1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

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Item		32-pin R5F10RBx	44-pin R5F10RFx	48-pin R5F10RGx	52-pin R5F10RJx	64-pin R5F10RLx
Code flash memory (KB)		8 to 32	8 to 32	8 to 32	8 to 32	16, 32
Data flash memory (KB)		2	2	2	2	2
RAM (KB)		1, 1.5 Note 1	1, 1.5 Note 1	1, 1.5 Note 1	1, 1.5 Note 1	1, 1.5 Note 1
Memory space		1 MB				
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) operation: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) operation: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) operation: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) operation: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)				
	High-speed on-chip oscillator clock	HS (high-speed main) operation: 1 to 24 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) operation: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) operation: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) operation: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)				
Subsystem clock		–	XT1 (crystal) oscillation , external subsystem clock input (EXCLKS) 32.768 kHz (TYP.): V_{DD} = 1.6 to 5.5 V			
Low-speed on-chip oscillator clock		Internal oscillation 15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V				
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)				
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: f_{IH} = 24 MHz operation)				
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)				
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)				
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.				
Total number of I/O port pins and pins dedicated to drive an LCD		28	40	44	48	58
I/O port	Total	20	29	33	37	47
	CMOS I/O	15	22	26	30	39
	CMOS input	3	5	5	5	5
	CMOS output	–	–	–	–	1
	N-ch open-drain I/O (EV_{DD} tolerance)	2	2	2	2	2
Pins dedicated to drive an LCD		8	11	11	11	11
LCD controller/driver		Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.				
	Segment signal output	13	22 (18) Note 2	26 (22) Note 2	30 (26) Note 2	39 (35) Note 2
	Common signal output	4	4 (8) Note 2			

Notes 1. In the case of the 1 KB, and 1.5 KB, this is 630 bytes when the self-programming function and data flash function is used.

2. The values in parentheses are the number of signal outputs when 8 com is used.

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60, P61				15.0 Note 2	mA
		Total of P10 to P14, P40 to P43, P120, P130, P140 to P147 (When duty = 70% Note 3)	4.0 V ≤ EV_{DD} ≤ 5.5 V			70.0	mA
			2.7 V ≤ EV_{DD} < 4.0 V			15.0	mA
			1.8 V ≤ EV_{DD} < 2.7 V			9.0	mA
			1.6 V ≤ EV_{DD} < 1.8 V			4.5	mA
		Total of P15 to P17, P30 to P32, P50 to P54, P60, P61, P70 to P74, P125 to P127 (When duty = 70% Note 3)	4.0 V ≤ EV_{DD} ≤ 5.5 V			80.0	mA
			2.7 V ≤ EV_{DD} < 4.0 V			35.0	mA
			1.8 V ≤ EV_{DD} < 2.7 V			20.0	mA
			1.6 V ≤ EV_{DD} < 1.8 V			10.0	mA
		Total of all pins (When duty = 70% Note 3)				150.0	mA
	I_{OL2}	P20, P21	Per pin			0.4	mA
			Total of all pins	1.6 V ≤ V_{DD} ≤ 5.5 V		0.8	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} and EV_{DD} pins to an output pin.

2. Do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 70.0 mA

Total output current of pins = (70.0 × 0.7)/(80 × 0.01) ≅ 61.25 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (1/3)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{IH} = 24 MHz Note 3	Basic operation	V_{DD} = 5.0 V		1.5		mA
						V_{DD} = 3.0 V		1.5		mA
					Normal operation	V_{DD} = 5.0 V		3.3	5.0	mA
						V_{DD} = 3.0 V		3.3	5.0	mA
				f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 5.0 V		2.5	3.7	mA
						V_{DD} = 3.0 V		2.5	3.7	mA
			LS (low-speed main) mode Note 5	f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.2	1.8	mA
						V_{DD} = 2.0 V		1.2	1.8	mA
			LV (low-voltage main) mode Note 5	f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.2	1.7	mA
						V_{DD} = 2.0 V		1.2	1.7	mA
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		2.8	4.4	mA
						Resonator connection		3.0	4.6	mA
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.8	4.4	mA
						Resonator connection		3.0	4.6	mA
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		1.8	2.6	mA
						Resonator connection		1.8	2.6	mA
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.8	2.6	mA
						Resonator connection		1.8	2.6	mA
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	mA
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V	Normal operation	Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = –40°C	Normal operation	Square wave input		3.5	4.9	μA
						Resonator connection		3.6	5.0	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		3.6	4.9	μA
						Resonator connection		3.7	5.0	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		3.7	5.5	μA
						Resonator connection		3.8	5.6	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		3.8	6.3	μA
						Resonator connection		3.9	6.4	μA
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		4.1	7.7	μA
						Resonator connection		4.2	7.8	μA

(**Notes** and **Remarks** are listed on the next page.)

Notes 1. Total current flowing into V_{DD} and EV_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD} or V_{SS}, EV_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator and subsystem clock are stopped.

4. When high-speed system clock and subsystem clock are stopped.

5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer, watchdog timer, and LCD controller/driver.

6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

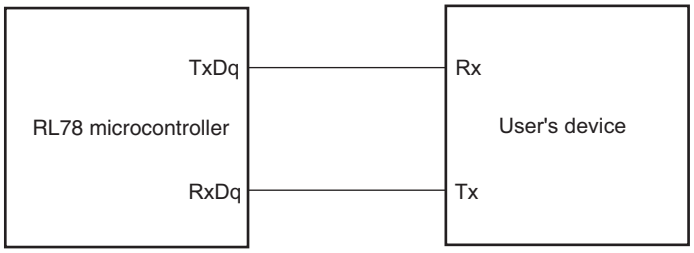
Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

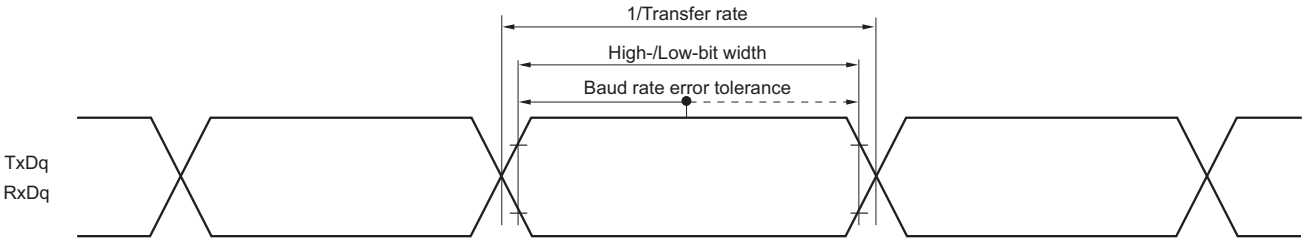
3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0), g: PIM and POM number (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 01))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time[Note 5]	t_{KCY2}	4.0 V ≤ EV_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ EV_{DD} < 4.0 V	16 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK}		6/f_{MCK}		ns
		1.8 V ≤ EV_{DD} < 2.4 V				6/f_{MCK}		6/f_{MCK}		ns
		1.6 V ≤ EV_{DD} < 1.8 V						6/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		ns
		2.7 V ≤ EV_{DD} < 4.0 V		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		ns
		2.4 V ≤ EV_{DD} < 2.7 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		ns
		1.8 V ≤ EV_{DD} < 2.4 V				t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		ns
		1.6 V ≤ EV_{DD} < 1.8 V						t_{KCY2}/2 – 66		ns
SIp setup time (to SCKp↑)[Note 1]	t_{SIK2}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ EV_{DD} < 2.7 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 40		ns
SIp hold time (from SCKp↑)[Note 2]	t_{KSI2}	2.4 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 250		ns

(**Notes**, **Caution,** and **Remarks** are listed on the next page.)

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) **(1/2)**

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.6	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.6	Mbps
			2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.6	Mbps
			1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V				f_{MCK}/6 Notes 1, 2		f_{MCK}/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3				1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. Use it with $EV_{DD} \geq V_b$.

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

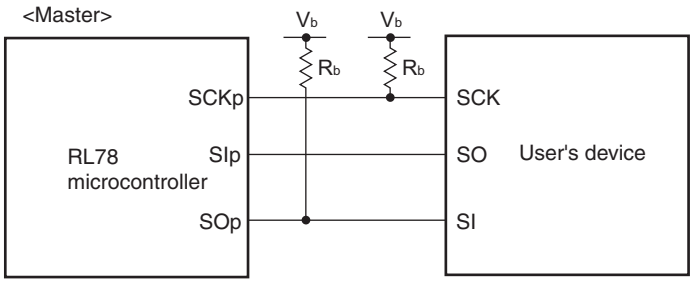
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (32-pin to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0), g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)

CSI mode connection diagram (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	20 MHz < f_{MCK} ≤ 24 MHz	12/f_{MCK}						ns
			8 MHz < f_{MCK} ≤ 20 MHz	10/f_{MCK}						ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	16/f_{MCK}						ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}						ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}						ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V	20 MHz < f_{MCK} ≤ 24 MHz	36/f_{MCK}						ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}						ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}						ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	4 MHz < f_{MCK} ≤ 8 MHz			16/f_{MCK}				ns
			f_{MCK} ≤ 4 MHz			10/f_{MCK}		10/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		t_{KCY2}/2 – 12		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2				t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	4.0 V ≤ EV_{DD} < 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2				1/f_{MCK} + 30		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}	4.0 V ≤ EV_{DD} < 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2				1/f_{MCK} + 31		1/f_{MCK} + 31		ns

(**Notes**, **Caution** and **Remarks** are listed on the next page.)

2.7 LCD Characteristics

2.7.1 Resistance division method

(1) Static display mode

(T_A = –40 to +85°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.0		V_{DD}	V

(2) 1/2 bias method, 1/4 bias method

(T_A = –40 to +85°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.7		V_{DD}	V

(3) 1/3 bias method

(T_A = –40 to +85°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.5		V_{DD}	V

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/3)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V_{DD}	V_{DD} = EV_{DD}	−0.5 to +6.5	V
	EV_{DD}	V_{DD} = EV_{DD}	−0.5 to +6.5	V
	EV_{SS}		−0.5 to +0.3	V
REGC pin input voltage	V_{IREGC}	REGC	−0.3 to +2.8 and −0.3 to V_{DD} + 0.3 Note 1	V
Input voltage	V_{I1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	−0.3 to EV_{DD} + 0.3 and −0.3 to V_{DD} + 0.3 Note 2	V
	V_{I2}	P60, P61 (N-ch open-drain)	−0.3 to EV_{DD} + 0.3 and −0.3 to V_{DD} + 0.3 Note 2	V
	V_{I3}	P20, P21, P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$	−0.3 to V_{DD} + 0.3 Note 2	V
Output voltage	V_{O1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P60, P61, P70 to P74, P120, P125 to P127, P130, P140 to P147	−0.3 to EV_{DD} + 0.3 and −0.3 to V_{DD} + 0.3 Note 2	V
	V_{O2}	P20, P21	−0.3 to V_{DD} + 0.3 Note 2	V
Analog input voltage	V_{AI1}	ANI16 to ANI23	−0.3 to EV_{DD} + 0.3 and −0.3 to AV_{REF}(+) + 0.3 Notes 2, 3	V
	V_{AI2}	ANI0, ANI1	−0.3 to V_{DD} + 0.3 and −0.3 to AV_{REF}(+) + 0.3 Notes 2, 3	V

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. AV_{REF}(+) : + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X)Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	MHz
XT1 clock oscillation frequency (f_{XT})Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **3.4 AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

3.2.2 On-chip oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{IH}			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85°C	2.4 V ≤ V_{DD} ≤ 5.5 V	–1		+1	%
		–40 to –20°C	2.4 V ≤ V_{DD} ≤ 5.5 V	–1.5		+1.5	%
		+85 to +105°C	2.4 V ≤ V_{DD} ≤ 5.5 V	–2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				–15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to **3.4 AC Characteristics** for instruction execution time.

Notes 1. Total current flowing into V_{DD} and EV_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD} or V_{SS}, EV_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, watchdog timer, and LCD controller/driver.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz

2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz

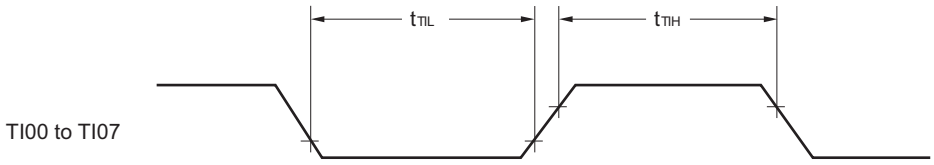
Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

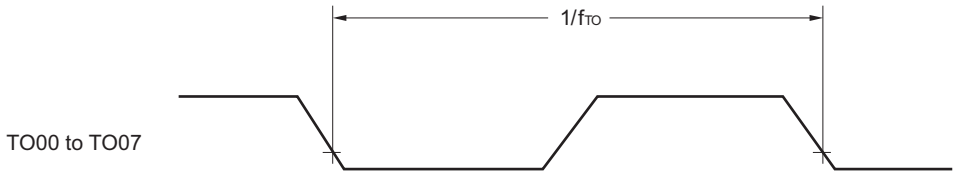
2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

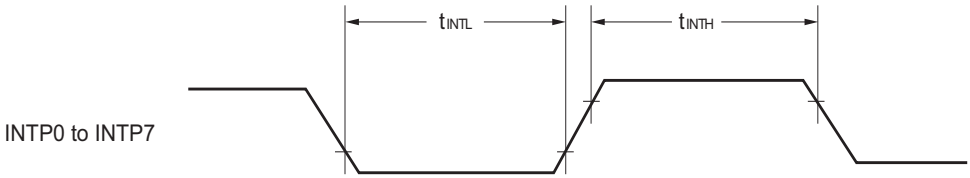
4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

TI/TO Timing

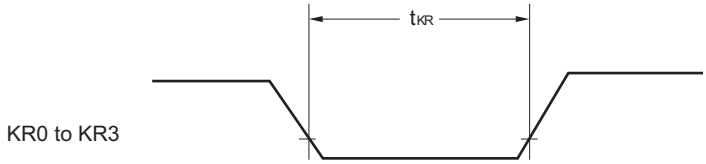




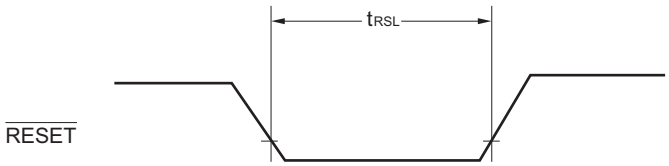
Interrupt Request Input Timing



Key Interrupt Input Timing

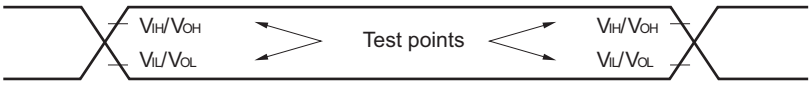


$\overline{\text{RESET}}$ Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1				f_{MCK}/12	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

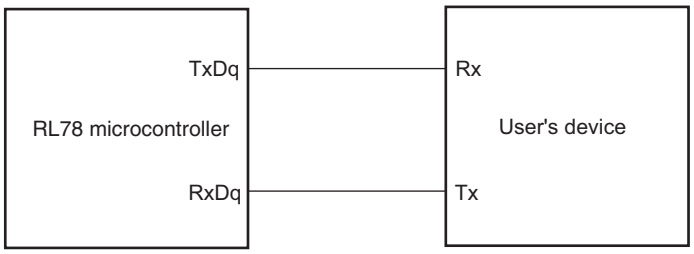
2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)

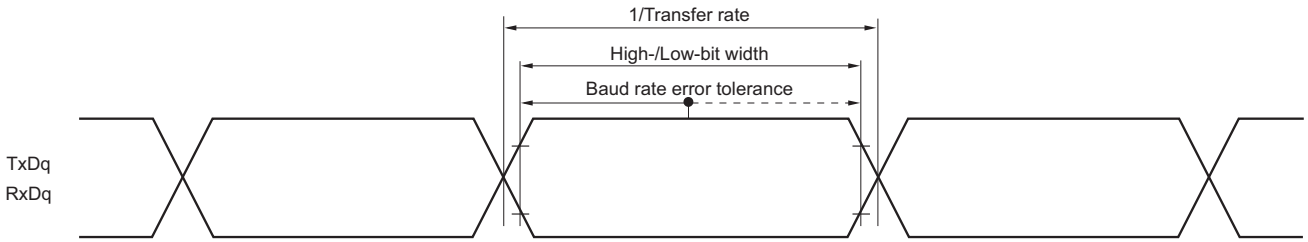
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0), g: PIM and POM number (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps
			2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (32- to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0), g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0, ANI1	–	Refer to **3.6.1 (3)**.	Refer to **3.6.1 (4)**.
ANI16 to ANI23	Refer to **3.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **3.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	2.4 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.25	%FSR
Integral linearity error [Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±2.5	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±1.5	LSB
Analog input voltage	V_{AIN}	Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 4]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 4]			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.
Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.
Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI16 to ANI23

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV_{REFP} = EV_{DD} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	t_{CONV}	10-bit resolution AV_{REFP} = EV_{DD} = V_{DD} Note 3	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	E_{ZS}	10-bit resolution AV_{REFP} = EV_{DD} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±0.35	%FSR
Full-scale error Notes 1, 2	E_{FS}	10-bit resolution AV_{REFP} = EV_{DD} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV_{REFP} = EV_{DD} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV_{REFP} = EV_{DD} = V_{DD} Note 3	2.4 V ≤ AV_{REFP} ≤ 5.5 V			±2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI23		0		AV_{REFP} and EV_{DD}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < EV_{DD} = V_{DD}, the MAX. values are as follows.
Overall error: Add ±4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV_{REFP} = V_{DD}.
Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

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